



STS1DN45K3

Dual N-channel 450 V, 3.2 Ω , 0.5 A SuperMESH3™
Power MOSFET in SO-8

Preliminary data

Features

Type	V _{DSS}	R _{DS(on)} max	I _D	P _w
STS1DN45K3	450 V	< 3.8 Ω	0.5 A	1.7 W

- 100% avalanche tested
- Low input capacitances and gate charge
- Low gate input resistance

Application

- Switching applications

Description

SuperMESH3™ is a new Power MOSFET technology that is obtained via improvements applied to STMicroelectronics' SuperMESH™ technology combined with a new optimized vertical structure. The resulting product has an extremely low on resistance, superior dynamic performance and high avalanche capability, making it especially suitable for the most demanding applications.

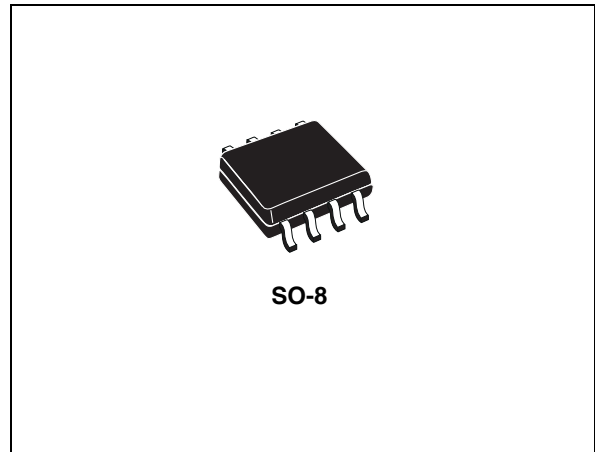


Figure 1. Internal schematic diagram

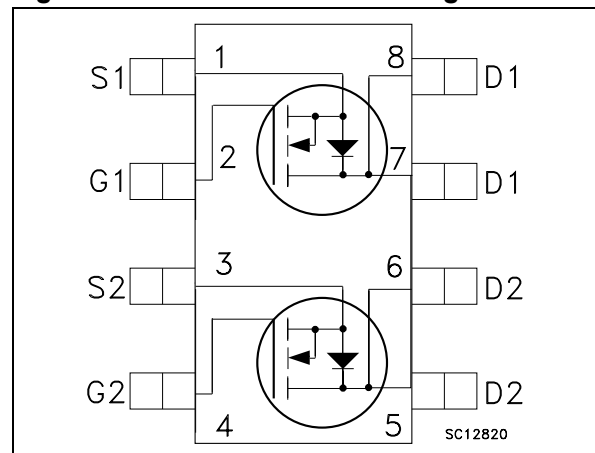


Table 1. Device summary

Order codes	Marking	Packages	Packaging
STS1DN45K3	1I45	SO-8	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	450	V
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	0.5	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	0.32	A
$I_{DM}^{(1)}$	Drain current (pulsed)	2	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$ (dual operation)	1.7	W
	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$ (single operation)	1.3	W
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	0.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	TBD	mJ
$dv/dt^{(2)}$	Peak diode recovery voltage slope	TBD	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^{\circ}\text{C}$
T_j	Max. operating junction temperature	150	$^{\circ}\text{C}$

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 0.5\text{ A}$, $di/dt \leq \text{TBD A}/\mu\text{s}$, $V_{Peak} < V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb max (single operation)	62.5	$^{\circ}\text{C}/\text{W}$
	Thermal resistance junction-amb max (dual operation)	78	$^{\circ}\text{C}/\text{W}$

1. When mounted on FR4 board (steady state)

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	450			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125\text{ °C}$			1 50	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 0.5\text{ A}$		3.2	3.8	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	150 30 6	-	pF pF pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }360\text{ V}$, $V_{GS} = 0$	-	TBD	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	TBD	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	TBD	-	Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 360\text{ V}$, $I_D = 0.5\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 3)	-	6 TBD TBD	-	nC nC nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 225\text{ V}$, $I_D = 0.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 4)	-	TBD	-	ns
t_r	Rise time			TBD		ns
$t_{d(off)}$	Turn-off-delay time			TBD		ns
t_f	Fall time			TBD		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		0.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				2	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 0.5\text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 0.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 7)	-	TBD		ns
Q_{rr}	Reverse recovery charge			TBD		nC
I_{RRM}	Reverse recovery current			TBD		A
t_{rr}	Reverse recovery time	$I_{SD} = 0.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 7)	-	TBD		ns
Q_{rr}	Reverse recovery charge			TBD		nC
I_{RRM}	Reverse recovery current			TBD		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-source breakdown voltage	$I_{gs} = \pm 1\text{ mA}$ (open drain)	30			V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components

3 Test circuits

Figure 2. Switching times test circuit for resistive load

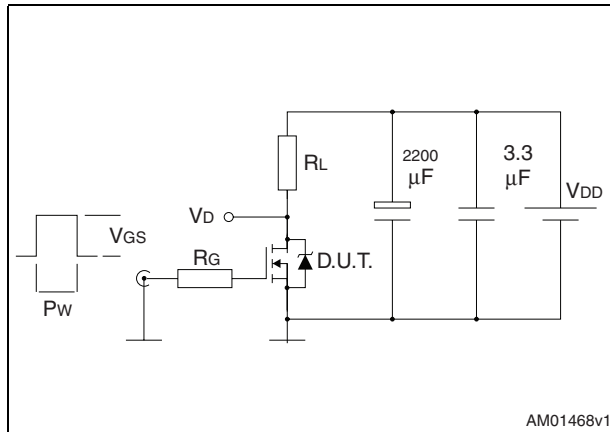


Figure 3. Gate charge test circuit

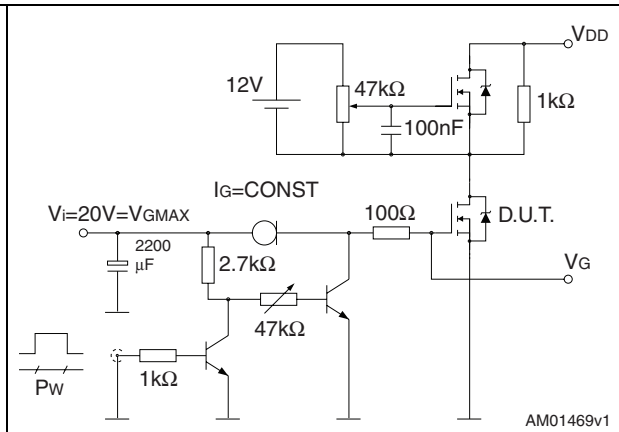


Figure 4. Test circuit for inductive load switching and diode recovery times

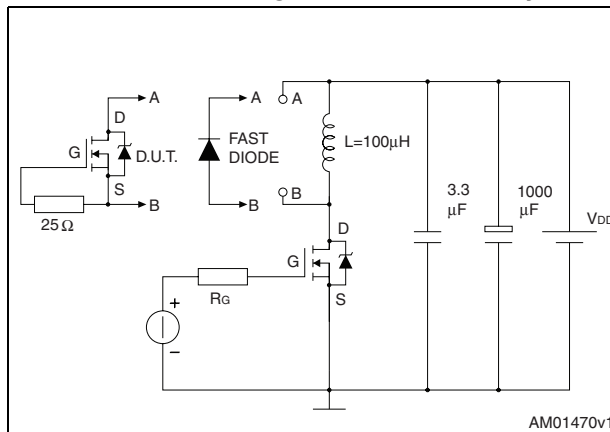


Figure 5. Unclamped inductive load test circuit

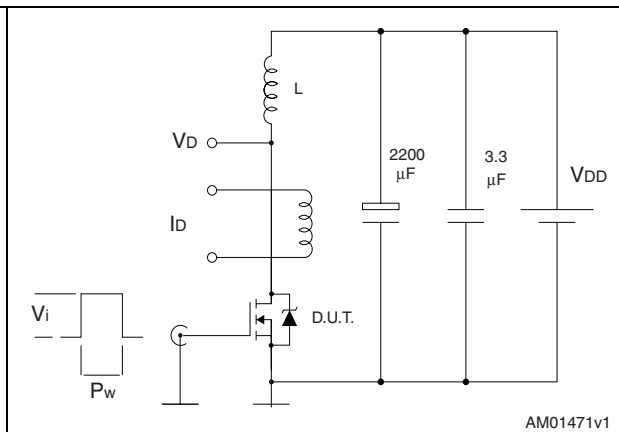


Figure 6. Unclamped inductive waveform

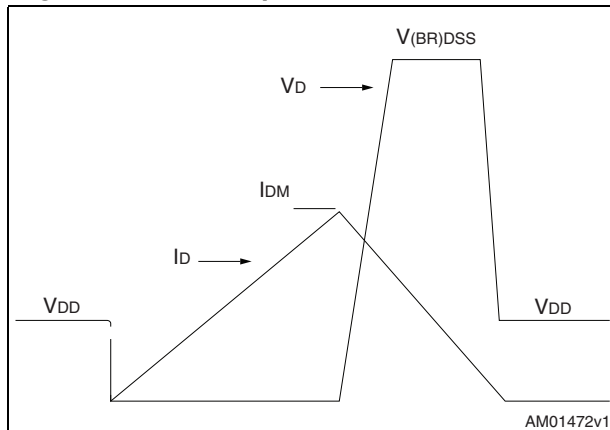
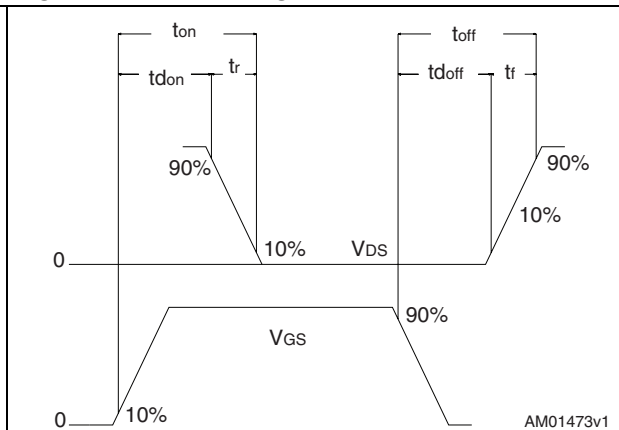


Figure 7. Switching time waveform

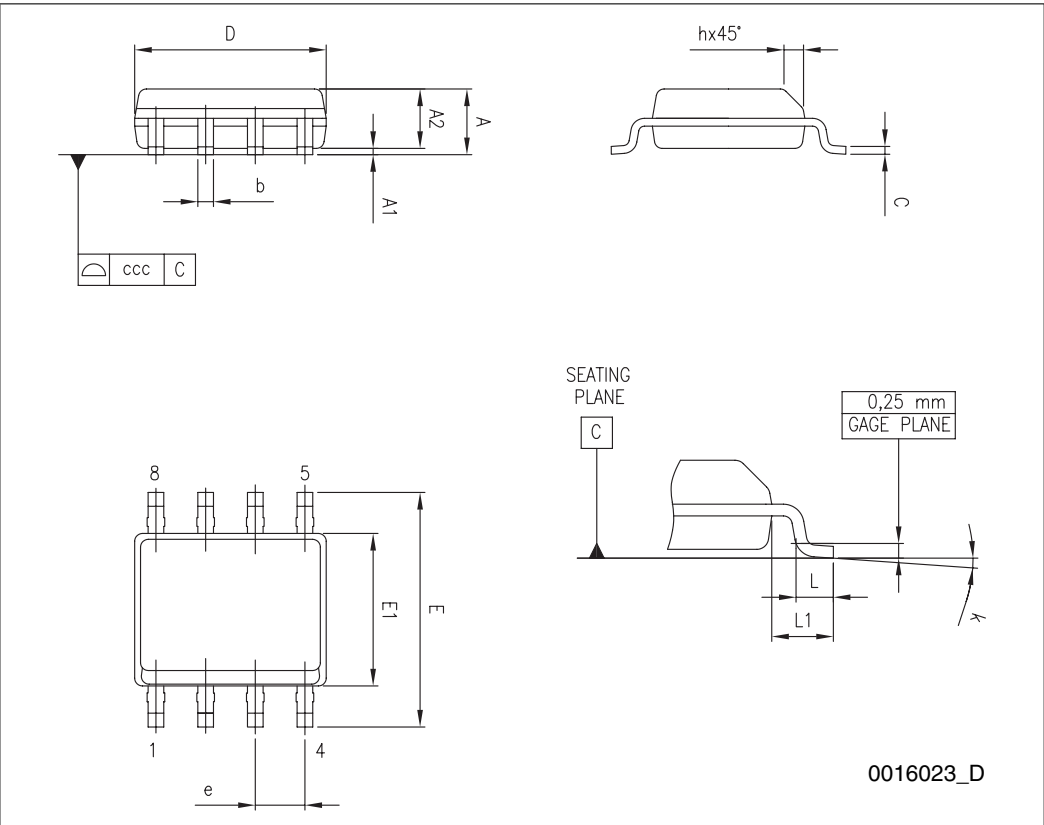


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

SO-8 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A			1.75
A1	0.10		0.25
A2	1.25		
b	0.28		0.48
c	0.17		0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e		1.27	
h	0.25		0.50
L	0.40		1.27
L1		1.04	
k	0°		8°
ccc			0.10



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
07-Apr-2010	1	First release

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